

J Rubio

List of Publications by Year in descending order

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42
all docs

42
docs citations

42
times ranked

337
citing authors

#	ARTICLE	IF	CITATIONS
1	Modeling arsenic deactivation through arsenic-vacancy clusters using an atomistic kinetic Monte Carlo approach. <i>Applied Physics Letters</i> , 2005, 86, 252103.	1.5	31
2	Optical admittance spectroscopy: A new method for deep level characterization. <i>Journal of Applied Physics</i> , 1987, 61, 2541-2545.	1.1	29
3	Physical atomistic kinetic Monte Carlo modeling of Fermi-level effects of species diffusing in silicon. <i>Physical Review B</i> , 2005, 72, .	1.1	27
4	Physical modeling and implementation scheme of native defect diffusion and interdiffusion in SiGe heterostructures for atomistic process simulation. <i>Journal of Applied Physics</i> , 2011, 109, .	1.1	27
5	Sulfur Hydrogen Bonding in Isolated Monohydrates: Furfuryl Mercaptan versus Furfuryl Alcohol. <i>Chemistry - A European Journal</i> , 2018, 24, 6564-6571.	1.7	27
6	Atomistic Monte Carlo simulations of three-dimensional polycrystalline thin films. <i>Journal of Applied Physics</i> , 2003, 94, 163-168.	1.1	23
7	Ion-beam amorphization of semiconductors: A physical model based on the amorphous pocket population. <i>Journal of Applied Physics</i> , 2005, 98, 046104.	1.1	21
8	Sulfur hydrogen bonding and internal dynamics in the monohydrates of thenyl mercaptan and thenyl alcohol. <i>Physical Chemistry Chemical Physics</i> , 2020, 22, 12412-12421.	1.3	21
9	An improved molecular dynamics scheme for ion bombardment simulations. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1995, 102, 7-11.	0.6	20
10	Modeling charged defects, dopant diffusion and activation mechanisms for TCAD simulations using kinetic Monte Carlo. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 253, 63-67.	0.6	19
11	Comprehensive model of damage accumulation in silicon. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	16
12	Physically based modelling of damage, amorphization, and recrystallization for predictive device-size process simulation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 151-155.	1.7	14
13	Dose effects on amorphous silicon sputtering by argon ions: A molecular dynamics simulation. <i>Journal of Applied Physics</i> , 1997, 81, 1488-1494.	1.1	13
14	An Efficient Microkinetic Modeling Protocol: Start with Only the Dominant Mechanisms, Adjust All Parameters, and Build the Complete Model Incrementally. <i>ACS Catalysis</i> , 2019, 9, 4804-4809.	5.5	13
15	Inâ€¦Diffusion and Annealing Kinetics of Palladium in Silicon. <i>Journal of the Electrochemical Society</i> , 1993, 140, 868-870.	1.3	12
16	Fermi-level effects in semiconductor processing: A modeling scheme for atomistic kinetic Monte Carlo simulators. <i>Journal of Applied Physics</i> , 2005, 98, 053709.	1.1	12
17	A DFT-Based Computational-Experimental Methodology for Synthetic Chemistry: Example of Application to the Catalytic Opening of Epoxides by Titanocene. <i>Journal of Organic Chemistry</i> , 2017, 82, 3760-3766.	1.7	12
18	Molecular Recognition, Transient Chirality and Sulfur Hydrogen Bonding in the Benzyl Mercaptan Dimer. <i>Symmetry</i> , 2021, 13, 2022.	1.1	11

#	ARTICLE	IF	CITATIONS
19	Kinetic Monte Carlo simulations: an accurate bridge between ab initio calculations and standard process experimental data. <i>Materials Science in Semiconductor Processing</i> , 2000, 3, 59-63.	1.9	9
20	Physically based modeling of dislocation loops in ion implantation processing in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 404-408.	1.7	7
21	Ion implant simulations: Kinetic Monte Carlo annealing assessment of the dominant features. <i>Applied Physics Letters</i> , 2004, 84, 4962-4964.	1.5	6
22	Physical modeling of Fermi-level effects for decanano device process simulations. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 284-289.	1.7	6
23	Dose loss and segregation of boron and arsenic at the Si/SiO ₂ interface by atomistic kinetic Monte Carlo simulations. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 392-396.	1.7	6
24	Atomistic modeling of defect diffusion and interdiffusion in SiGe heterostructures. <i>Thin Solid Films</i> , 2010, 518, 2448-2453.	0.8	6
25	Computer simulation of point-defect distributions generated by ion implantation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993, 80-81, 172-175.	0.6	5
26	Comprehensive, physically based modelling of As in Si. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 135-140.	1.7	5
27	Constant-capacitance deep-level optical spectroscopy. <i>Solid-State Electronics</i> , 1989, 32, 287-293.	0.8	4
28	Detailed computer simulation of ion implantation processes into crystals. <i>Materials Science and Technology</i> , 1995, 11, 1191-1193.	0.8	4
29	Comprehensive modeling of ion-implant amorphization in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 383-385.	1.7	4
30	Rotational spectra of tetracyclic quinolizidine alkaloids: does a water molecule flip sparteine?. <i>Physical Chemistry Chemical Physics</i> , 2017, 19, 17553-17559.	1.3	4
31	Monte Carlo Atomistic Simulation of Polycrystalline Aluminum Deposition. <i>Materials Research Society Symposia Proceedings</i> , 1998, 514, 127.	0.1	3
32	Optical capture cross sections of palladium in silicon. <i>Journal of Applied Physics</i> , 1991, 69, 298-301.	1.1	2
33	A kinetic Monte Carlo annealing assessment of the dominant features from ion implant simulations. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 345-348.	1.7	2
34	15-Hydroxygermacranolides as Sources of Structural Diversity: Synthesis of Sesquiterpene Lactones by Cyclization and Rearrangement Reactions. Experimental and DFT Study. <i>Journal of Organic Chemistry</i> , 2018, 83, 5480-5495.	1.7	2
35	Molecular dynamics simulations of ion bombardment processes. <i>Materials Science and Technology</i> , 1997, 13, 893-896.	0.8	1
36	Chirality-Puckering correlation and intermolecular interactions in Sphingosines: Rotational spectroscopy of jaspine B3 and its monohydrate. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , 2021, 267, 120531.	2.0	1

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37	<i>cis</i> and <i>trans</i> platinum(<i>ii</i>) N-heterocyclic carbene isomers: synthesis, characterization and biological activity. <i>New Journal of Chemistry</i> , 2022, 46, 14221-14226.	1.4	1
38	Bimodal distribution of damage morphology generated by ion implantation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 389-391.	1.7	0
39	Ion-implant simulations: The effect of defect spatial correlation on damage accumulation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 386-388.	1.7	0
40	Current Capabilities and Future Prospects of Atomistic Process Simulation. , 2007, , .		0
41	Rotational spectroscopy of organophosphorous chemical agents: cresyl and phenyl saligenin phosphates. <i>Physical Chemistry Chemical Physics</i> , 2019, 21, 16418-16422.	1.3	0